Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-106-1607

| In | closure Material: |
|----|---|
| GI | lass and metal |
| 0 | verall Length: |
| 0. | 340 inches |
| 0 | verall Diameter: |
| 0. | 187 inches |
| M | ounting Facility Quantity: |
| 1 | |
| M | ounting Method: |
| Te | erminal and threaded stud |
| Fe | eatures Provided: |
| He | ermetically sealed case |
| 0 | verall Width Across Flats: |
| 0. | 187 inches |
| Tł | nread Size: |
| 0. | 112 inches |
| Se | emiconductor Material: |
| Si | licon |
| Vo | oltage Rating In Volts Per Characteristic: |
| 60 | 00.0 reverse voltage, peak |
| С | urrent Rating Per Characteristic: |
| 12 | 2.00 amperes average forward current averaged over a full 60-hz cycle |
| M | aximum Operating Tempurature Per Measurement Point: |
| 10 | 00.0 degrees celsius case |
| Tł | nread Series Designator: |
| Uı | nf |
| Te | erminal Type And Quantity: |
| 1 | threaded stud and 1 binding post |
| Sł | nelf Life: |
| N/ | 'a |
| Uı | nit Of Measure: |
| | |
| De | emilitarization: |
| No | 0 |
| Fi | ig: |
| A٢ | 110a0 |